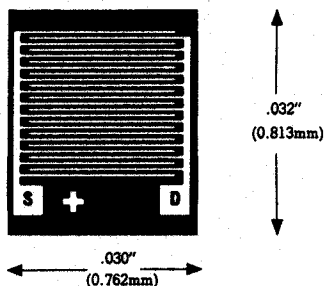


CHIP NUMBER

FN9.1



Die Size: 30 x 32 (mils)
0.762 x .813(mm)
Pad Size: .762 x .813(mils)
0.102 x 0.102(mm)
GATE-SUBSTRATE

CONTACT METALLIZATION

Top Contact: > 12,000
Å Aluminum

Backside Contact: 3,000 Å Gold

ASSEMBLY RECOMMENDATIONS

It is advisable that:

- the die be eutectically mounted with gold silicon preform 98/2%.
- 1 mil (0.0254mm) aluminum wire be ultrasonically attached to the top contact.

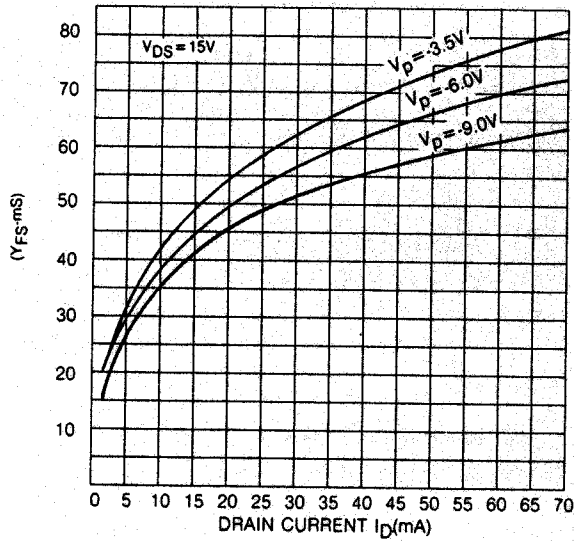
TYPICAL ELECTRICAL CHARACTERISTICS

PARAMETER	MIN.	TYP	MAX.	UNIT	TEST CONDITIONS
BVGSS	- 25	- 40	- 50	V	$V_{DS} = 0, I_G = 1\mu A$
I_{DSS}	30		1000	mA	$V_{DS} = 15V, V_{GS} = 0$
V_p	-1.0		-10	V	$V_{DS} = 5V, I_D = 1nA$
R_{on}	3.5		15	OHms	$V_{GS} = 0, I_D = 10mA$
I_{GSS}		30	200	pA	$V_{DS} = 0, V_{GS} = -15V$
C_{iss}		28	50	pF	$V_{DS} = 0, V_{GS} = -10V, f = 1MHz$
C_{rss}		14	25	pF	$V_{DS} = 0, V_{GD} = 10V, f = 1MHz$
g_{fs}	75	120	250	ms	$V_{DS} = 15V, V_{GS} = 0, f = 1KHz$

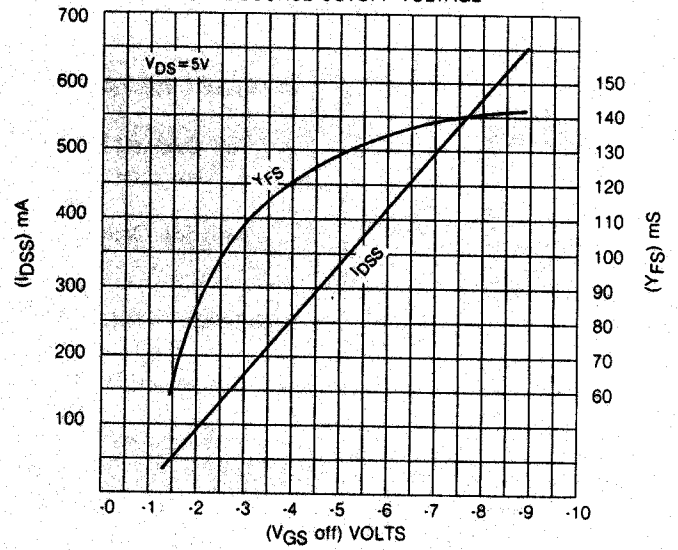
TYPICAL DEVICE TYPES: 2N5432 - 2N5434, series

CHIP TYPE FN9.1

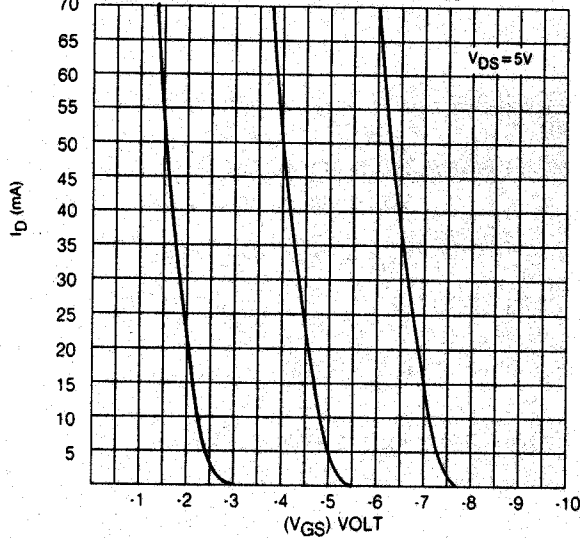
**FORWARD TRANSADMITTANCE
VS. OPERATING DRAIN CURRENT**



**FORWARD TRANSADMITTANCE VS
GATE-SOURCE CUTOFF VOLTAGE**



TRANSFER CHARACTERISTICS



OUTPUT CHARACTERISTICS

